

N-Channel 800 V (D-S) Super Junction Power MOSFET



RoHS
COMPLIANT

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A)	Q_g (Typ.)
800	150 at $V_{GS} = 10$ V	18	54 nC

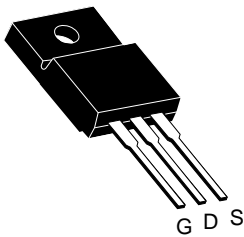
FEATURES

- DT-SJ Power MOSFET
- 100 % Rg and UIS tested
- Low $R_{DS(ON)} \times FOM$
- Extremely low switching loss
- Excellent stability and uniformity

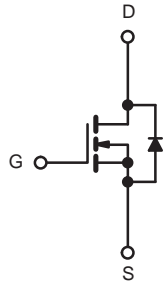
APPLICATIONS

- PC power
- Telecom power
- Server power
- LED Light
- EV Charger

TO-220 FULLPAK



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage(Typ.)	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_C = 25$ °C	18
		$T_C = 100$ °C	11.4
Pulsed Drain Current ^b	I_{DM}	39	A
Single Avalanche Energy ^e	E_{AS}	245	mJ
Maximum Power Dissipation ^c	P_D	$T_C = 25$ °C	34
		$T_C = 100$ °C	13.6
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^d	R_{thJA}	62	°C/W
Junction-to-Case (Drain)	R_{thJC}	3.67	

Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P_d is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{thJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25$ °C.
- $V_{DS} = 100$ V, $V_{GS} = 10$ V, $L = 80$ mH, starting $T_J = 25$ °C.

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	800	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.9	-	3.9	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	μA
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	-	150	200	m Ω
		$V_{GS} = 10\text{ V}, I_D = 9\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	420	-	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 9\text{ A}$	-	15	-	S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 100\text{ KHz}$	-	2620	-	pF
Output Capacitance	C_{oss}		-	111	-	
Reverse Transfer Capacitance	C_{rss}		-	4.4	-	
Total Gate Charge ^c	Q_g	$V_{DS} = 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	-	54	-	nC
Gate-Source Charge ^c	Q_{gs}		-	11	-	
Gate-Drain Charge ^c	Q_{gd}		-	17	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	-	17.2	-	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 9\text{ A},$ $V_{GEN} = 10\text{ V}, R_g = 2\text{ }\Omega$	-	28	-	ns
Rise Time ^c	t_r		-	17	-	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	146	-	
Fall Time ^c	t_f		-	18	-	
Drain-Source Body Diode Ratings and Characteristics ^b ($T_C = 25\text{ }^\circ\text{C}$)						
Continuous Source Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	18	A
Pulsed Current ($t = 100\text{ }\mu\text{s}$)	I_{SM}		-	-	39	A
Forward Voltage ^a	V_{SD}	$I_S = 18\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.3	V
Reverse Recovery Time	t_{rr}	$I_S = 9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	342	-	ns
Reverse Recovery Charge	Q_{rr}		-	5	-	μC
Peak reverse recovery current	I_{rrm}		-	29	-	A

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

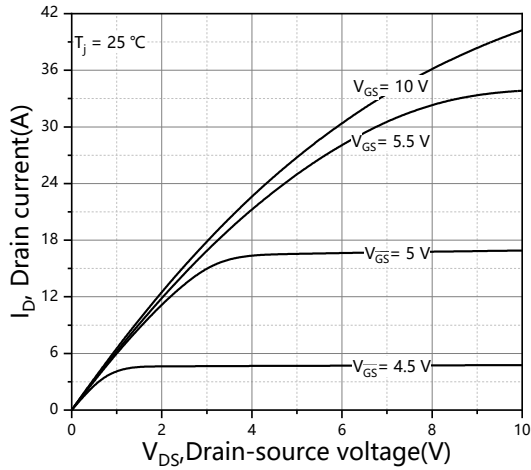


Figure 1. Typ. output characteristics

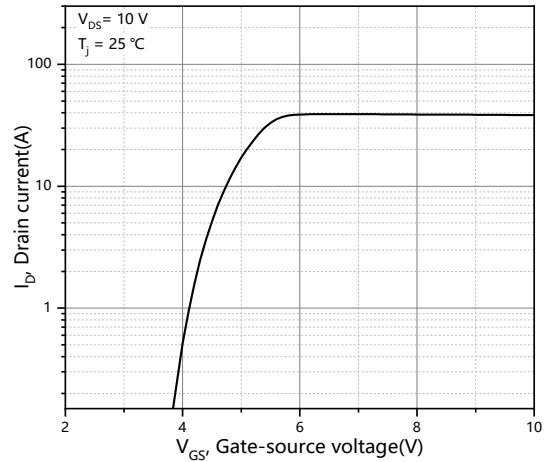


Figure 2. Typ. transfer characteristics

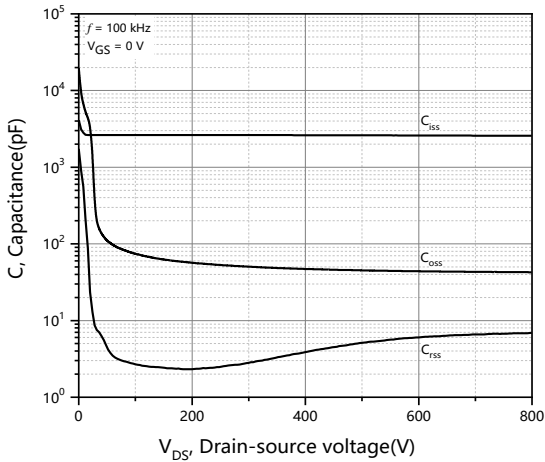


Figure 3. Typ. capacitances

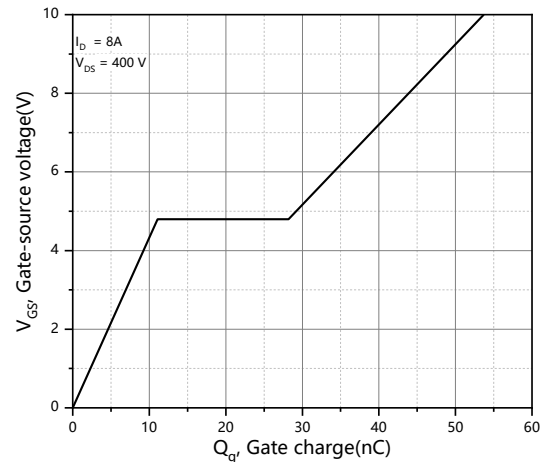


Figure 4. Typ. gate charge

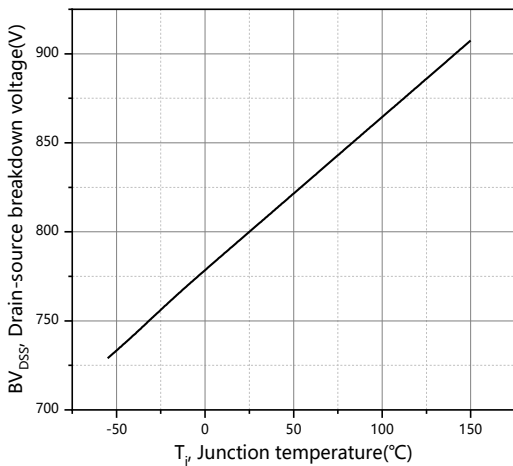


Figure 5. Drain-source breakdown voltage

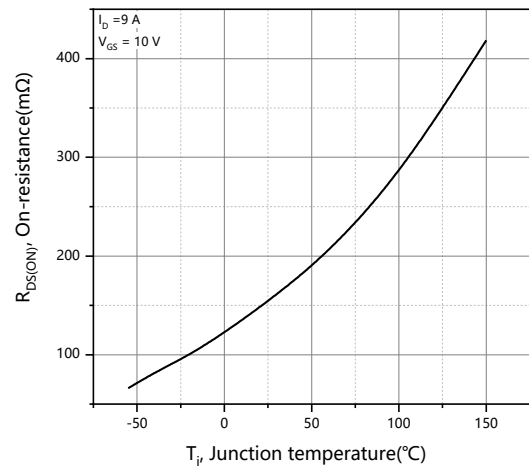


Figure 6. Drain-source on-state resistance

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

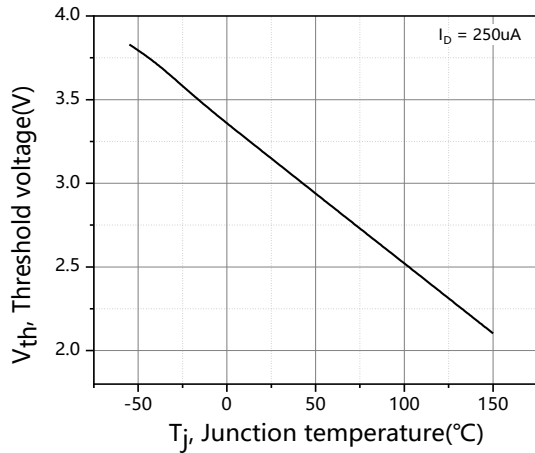


Figure 7. Threshold voltage

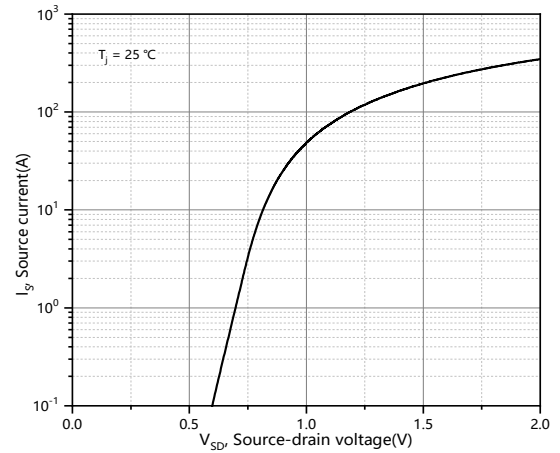


Figure 8. Forward characteristic of body diode

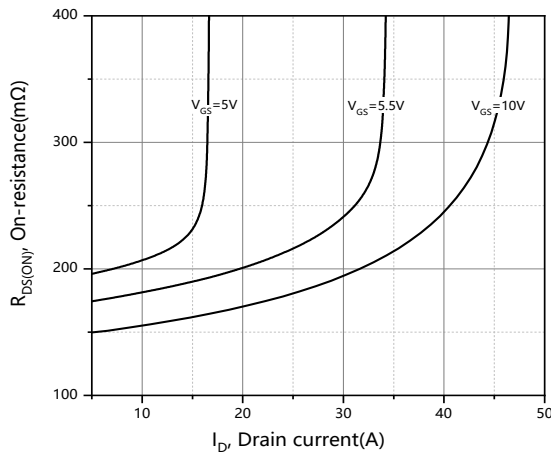


Figure 9. Drain-source on-state resistance

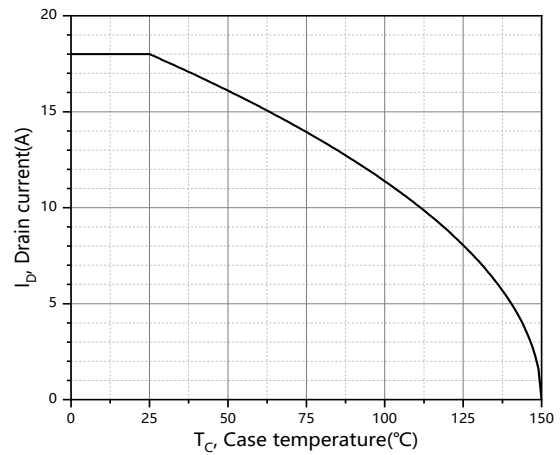


Figure 10. Drain current

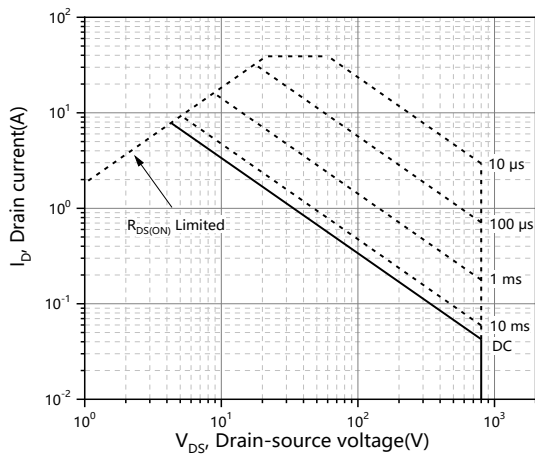


Figure 11. Safe operation area $T_C=25\text{ }^\circ\text{C}$

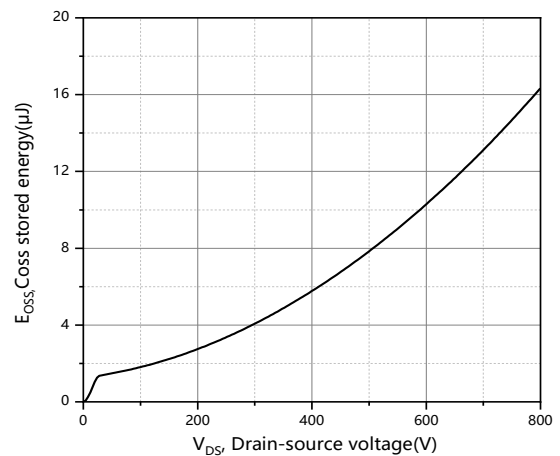


Figure 12. Typ. Coss stored energy

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

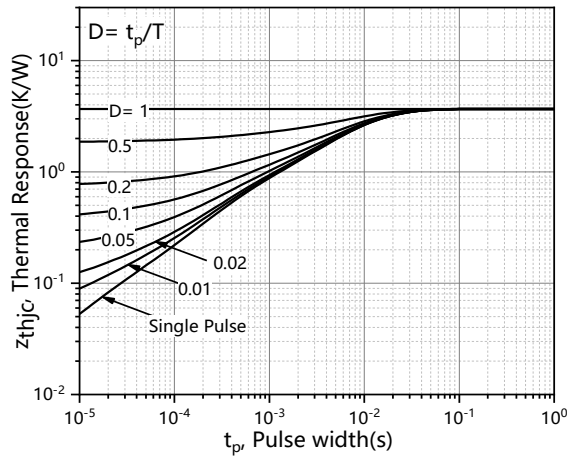
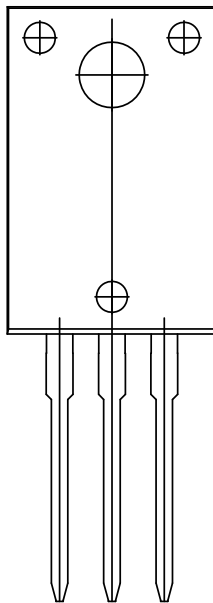
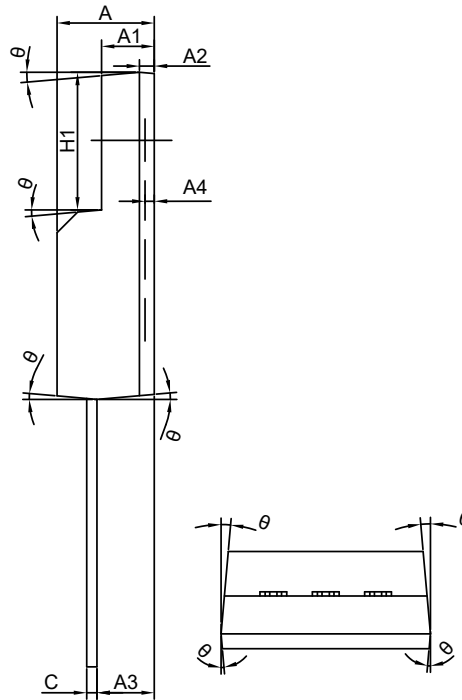
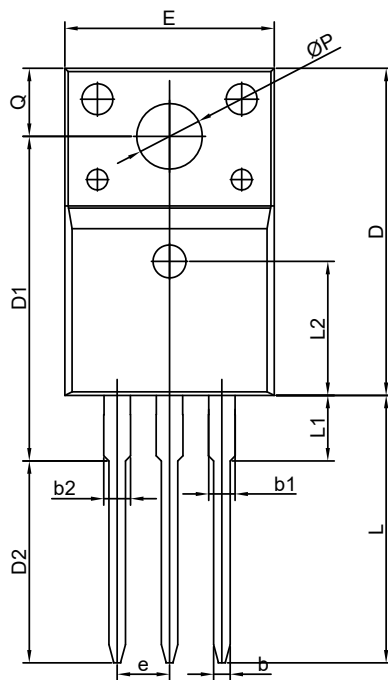


Figure 13. Max.transient thermal impedance

TO-220F-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.30	4.72	5.10
A1	2.25	2.56	2.90
A2	0.72 REF		
A3	2.28	2.78	3.50
A4	0.45 MAX		
b	0.65	-	0.95
b1	1.00	-	1.55
b2	-	-	1.55
c	0.40	0.50	0.65
D	15.47	15.87	16.37
D1	15.35	15.75	16.25
E	9.76	10.16	10.76
e	2.54 BSC		
H1	6.28	6.68	7.08
L	12.48	12.98	13.50
L1	2.90	-	3.80
L2	2.54 BSC		
ØP	2.98	3.18	3.50
Q	3.00	-	3.60
θ	3°	5°	7°

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